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3/20/3  
SurlesIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: K. TORII, et al.  
Application No.: 09/391,250  
Filed: September 7, 1999  
For: MEMORY STRUCTURE WITH A FERROELECTRIC CAPACITOR AND A FABRICATION METHOD THEREOF (As amended)  
Group: 2811  
Examiner: C. Nguyen

AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

May 12, 2003

Sir:

In response to the Office Action dated January 10, 2003, the period of response for

05/21/2003 SSURLES/whd/extension is requested by the attached Petition for Extension of Time, please amend  
Sale Ref: 00000004 DAH: 012135 09391250  
01 FC:1202 72.00 CH  
02 FC:1201 168.00 CH  
the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 7 as follows:

1. (Twice Amended) A semiconductor device comprising:  
an insulating film formed on a substrate provided with a transistor and having an opening portion;  
a conductive film formed in the opening portion; and